

SIPR-3251-6.0

DOF

Si Substrate



Film Thickness: 6.0 μ m Prebake: 100°Cx120 sec
Exp.: 450mJ/cm² (I-g-line, NA = 0.35, σ = 0.60)
Mask: 1.5 μ m L/S Focus: -3.0 ~ +2.0 μ m PEB: none
Dev.: 50 sec x 3 puddles (SSF2-238)

